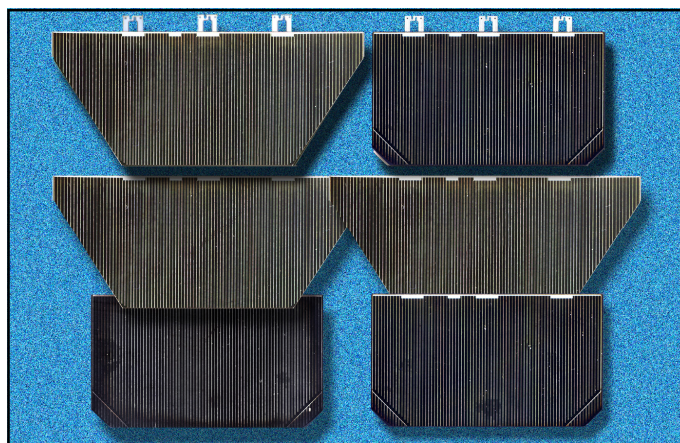


25.1% GaInP₂/GaAs/Ge Triple Junction Solar Cells

Features

- High efficiency n/p design
 - BOL: up to 26% minimum average efficiency (28°C, AM0)
 - EOL: up to 21% minimum average efficiency (28°C, AM0, 1E15 e/cm² 1 MeV equivalence)
 - Integral bypass diode protection
 - Transparent insertion into existing systems
- High volume production capability:
 - Currently delivering 24.5% min. avg. efficiency solar cells
 - 26% minimum average efficiency available in year 2000



Product Description

Substrate	Germanium
Method of GaAs Growth	Metal Organic Vapor Phase Epitaxy
Device Design	Monolithic, two terminal triple junction. n/p GaInP ₂ , GaAs, and Ge solar cells interconnected with two tunnel junctions
Sizes	Up To 30 cm ²
Assembly Method	Multiple techniques including soldering, welding, thermocompression, or ultrasonic wire bonding
Integral Diode	Si diode integrated into recess on back side

Note: Other Variations Are Available Upon Request

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Heritage

- More than 2000 kW of multi-junction cells produced
- More than 675 kW of multi-junction arrays *on orbit*
- 1 MW annual capacity - cells, panels & arrays
- On orbit performance for multi-junction solar cells validated to ± 1.5% of ground test results

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Typical Electrical Parameters

(AMO (135.3 mW/cm²) 28 °C, Bare Cell)

$$J_{sc} = 15.60 \text{ mA/cm}^2$$

$$J_{mp} = 14.90 \text{ mA/cm}^2$$

$$J_{load \text{ min avg}} = 14.93 \text{ mA/cm}^2$$

$$V_{oc} = 2.545 \text{ V}$$

$$V_{mp} = 2.275 \text{ V}$$

$$V_{load} = 2.220 \text{ V}$$

$$C_{ff} = 0.85$$

$$Eff_{load} = 24.5\%$$

$$Eff_{mp} = 25.1\%$$

Radiation Degradation

(Fluence 1MeV Electrons/cm²)

Parameters	1x10 ¹⁴	3x10 ¹⁴	1x10 ¹⁵
I _{mp} /I _{mp0}	0.99	0.97	0.90
V _{mp} /V _{mp0}	0.97	0.95	0.92
P _{mp} /P _{mp0}	0.96	0.92	0.83

Thermal Properties

Solar Absorptance= 0.92 (Ceria Doped Microsheet)

Emissance (Normal)= 0.85 (Ceria Doped Microsheet)

Temperature Coefficients

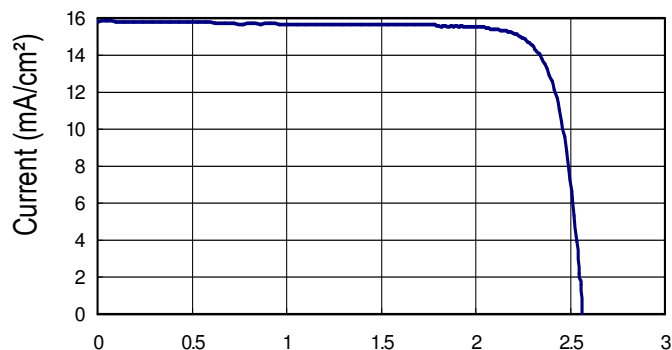
Parameters	BOL	1x10 ¹⁵ (1 MeV e/cm ²)
J _{mp} (μA/cm ² /°C)	6	14
J _{sc} (μA/cm ² /°C)	9	11
V _{mp} (mV/°C)	-6.7	-7.2
V _{oc} (mV/°C)	-6.4	-6.8

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The information contained on this sheet is for reference only.
Specifications subject to change without notice. 4/29/2008

Typical IV Characteristic

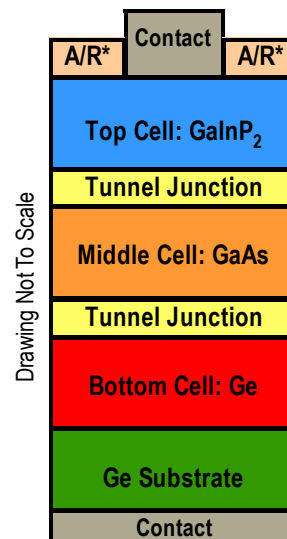
AMO (135.3 mW/cm²) 28 °C, Bare Cell



Weight

84 mg/ cm² (Bare) @ 140 μm (5.5 mil) Thickness

Thickness of 175 μm typical with weight equivalence of a 140 μm thick cell.



*A/R: Anti-Reflective Coating

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